

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PATENT APPLICATION

Inventors: Douglas J. Tweet, Sheng Teng Hsu,
and Jer-Shen Maa

Serial No: Not Yet Assigned

Attorney Docket No.
SLA0586

Filed: Herewith

Title: METHOD TO FORM LOCAL
SILICON-ON-NOTHING OR
SILICON-ON-INSULATOR WAFERS
WITH TENSILE-STRAINED SILICON

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

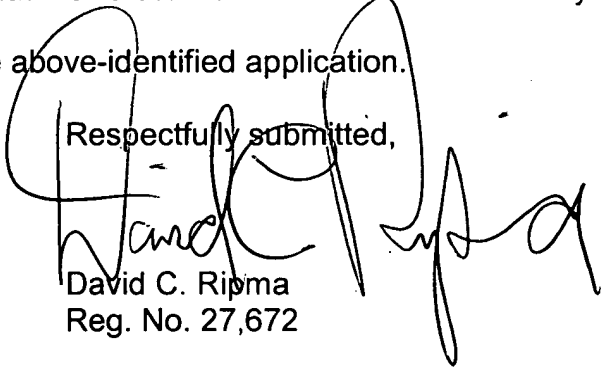
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

March 23, 2004
(Date)

Respectfully submitted,


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Disclosure SLA0586



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| 1449A/PTO Rev. 10/95 | | U.S. Department of Commerce Patent and Trademark Office | | Complete If Known | |
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| | | | | Filing Date | 03-23-04 |
| | | | | First Named Inventor | Douglas James Tweet |
| | | | | Group Art Unit | |
| | | | | Examiner Name | |
| LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary) | | | | Attorney Docket No. | SLA.0586 |
| | | | | Sheet 1 of 1 | |

| OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS | | | |
|--|-----------------------|---|----------------|
| Examiner Initials | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source. | T ² |
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|--------------------|--|-----------------|--|
| Examiner Signature | | Date Considered | |
|--------------------|--|-----------------|--|

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
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